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20 V, single N-channel Trench MOSFET 13 November 2012

Product data sheet

## 1. Product profile

#### 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a SOT363 (SC-88) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### **1.2 Features and benefits**

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology

#### **1.3 Applications**

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	-	3.3	А
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C		-	45	55	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.





20 V, single N-channel Trench MOSFET

## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	6 5 4	D
2	D	drain		
3	G	gate		G UT 4
4	S	source	∐1 ∐2 ∐3	S 017aaa253
5	D	drain	TSSOP6 (SOT363)	017444255
6	D	drain		

## 3. Ordering information

Table 3. Ordering information					
Type number Package					
	Name	Description	Version		
PMG45UN	TSSOP6	plastic surface-mounted package; 6 leads	SOT363		

## 4. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMG45UN	U5%

[1] % = placeholder for manufacturing site code

## 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

drain-source voltage	T <sub>i</sub> = 25 °C				_
	J		-	20	V
gate-source voltage			-8	8	V
drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	3.3	А
	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	3	А
	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	1.9	А
peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	12	А
total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	375	mW
		[1]	-	715	mW
-	drain current peak drain current total power dissipation	$\begin{array}{c} V_{GS} = 4.5 \text{ V};  \text{T}_{amb} = 25 ^{\circ}\text{C};  \text{t} \leq 5 \text{ s} \\ \hline V_{GS} = 4.5 \text{ V};  \text{T}_{amb} = 25 ^{\circ}\text{C} \\ \hline V_{GS} = 4.5 \text{ V};  \text{T}_{amb} = 100 ^{\circ}\text{C} \\ \hline \text{Peak drain current} \\ \end{array}$	$\begin{array}{ c c c c c } \hline & & & & & & & & & & & & & & & & & & $	$ \begin{array}{c c} \mbox{drain current} & V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C; \ t \leq 5 \ s & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 100 \ ^{\circ}C & [1] & - \\ \hline V_{GS} = 4.5 \ V; \ T_{amb} = 100 \ ^{\circ}C & [1] & - \\ \hline peak \ drain \ current & T_{amb} = 25 \ ^{\circ}C; \ single \ pulse; \ t_p \leq 10 \ \mu s & - \\ \hline total \ power \ dissipation & T_{amb} = 25 \ ^{\circ}C & [1] & - \\ \hline \hline 1 & - & \\ \hline \end{array} $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

## PMG45UN

#### 20 V, single N-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Мах	Unit
		T <sub>sp</sub> = 25 °C		-	4350	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.8	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

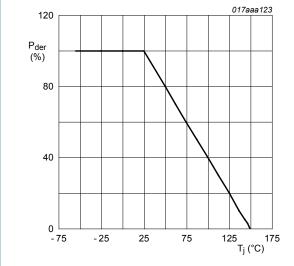


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

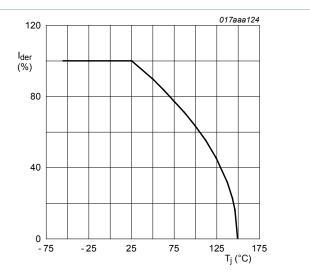
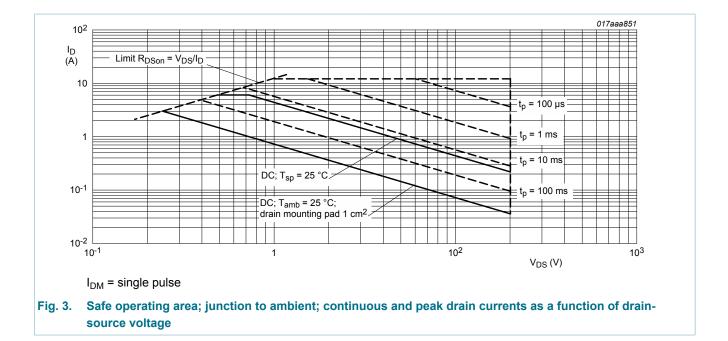


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

#### 20 V, single N-channel Trench MOSFET



## 6. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance		in free air	[1]	-	289	332	K/W
from junction to ambient			[2]	-	152	175	K/W
ampient	ambient		[3]	-	117	145	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	25	29	K/W

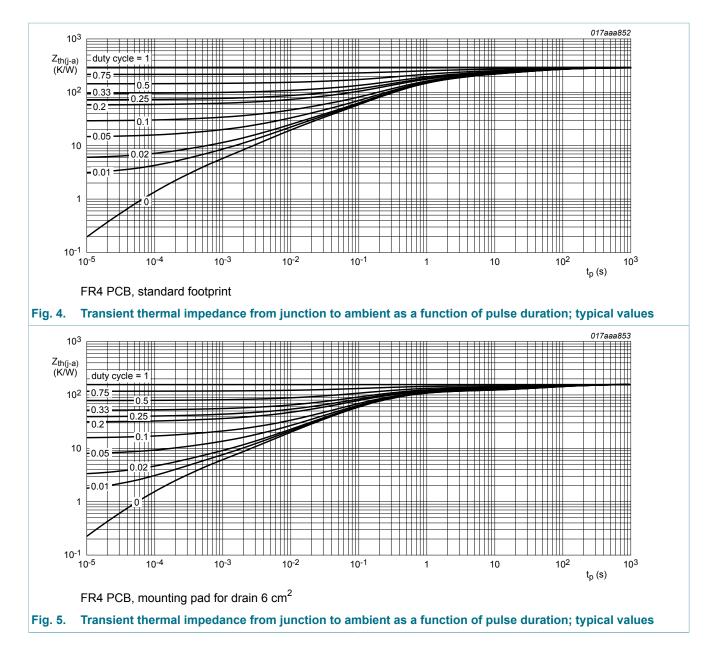
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>, t  $\leq$  5 s.

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#### 20 V, single N-channel Trench MOSFET



## 7. Characteristics

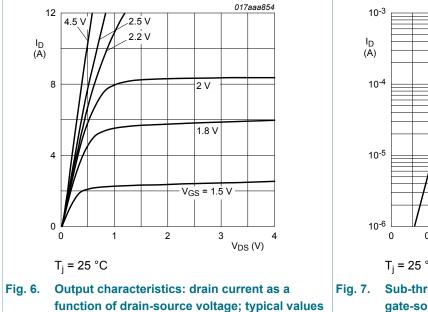
Table 7. C	haracteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static characteristics							
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C		20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C		0.4	0.7	1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C		-	-	100	nA
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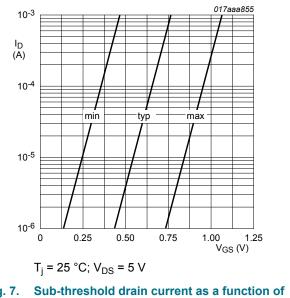
Product data sheet

## PMG45UN

#### 20 V, single N-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C	-	45	55	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 150 °C	-	66	81	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 2.5 A; T <sub>j</sub> = 25 °C	-	58	76	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 0.8 A; T <sub>j</sub> = 25 °C	-	85	125	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C	-	11.2	-	S
Dynamic c	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; I <sub>D</sub> = 3 A; V <sub>GS</sub> = 4.5 V;	-	2.2	3.3	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.32	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.56	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	184	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	51	-	pF
C <sub>rss</sub>	reverse transfer capacitance	_	-	29	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; I <sub>D</sub> = 3 A; V <sub>GS</sub> = 4.5 V;	-	8	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	30	-	ns
t <sub>f</sub>	fall time		-	26	-	ns
Source-dra	iin diode	·				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 0.8 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C	-	0.8	1.2	V

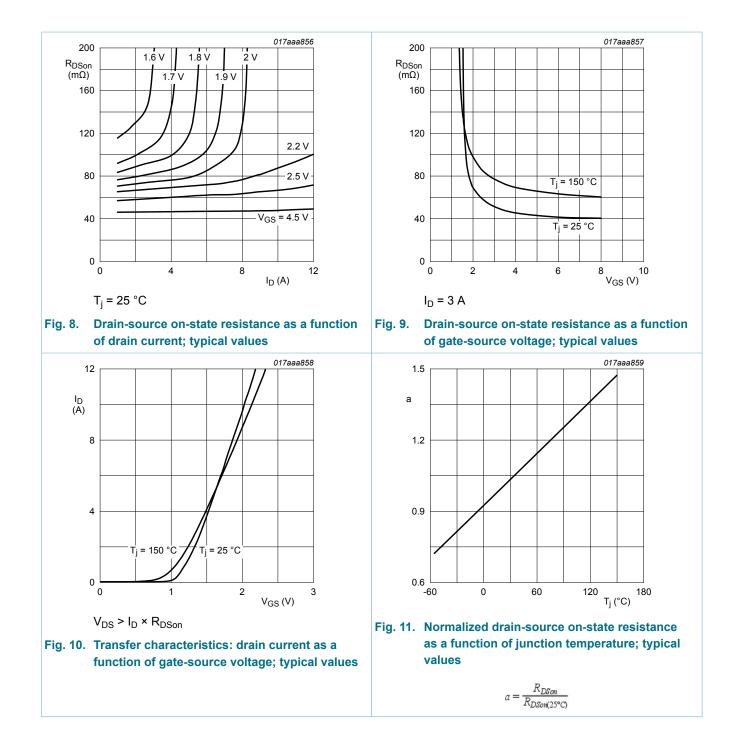




gate-source voltage

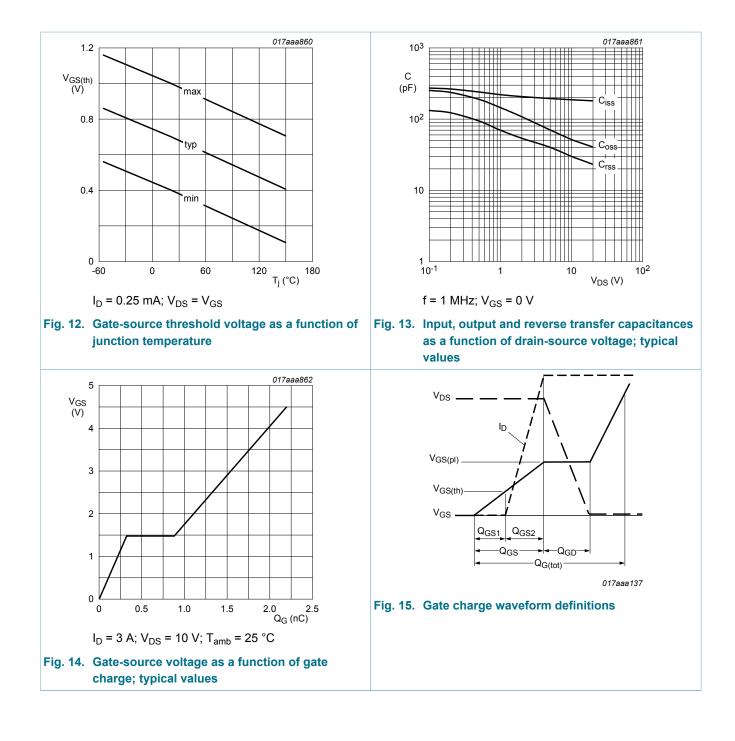
## PMG45UN

#### 20 V, single N-channel Trench MOSFET



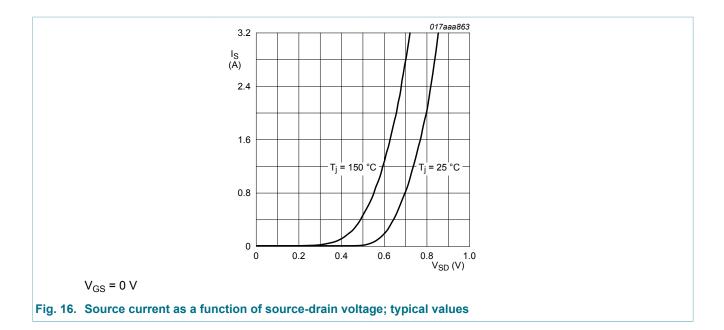
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#### 20 V, single N-channel Trench MOSFET

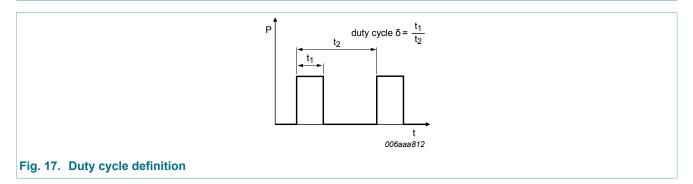


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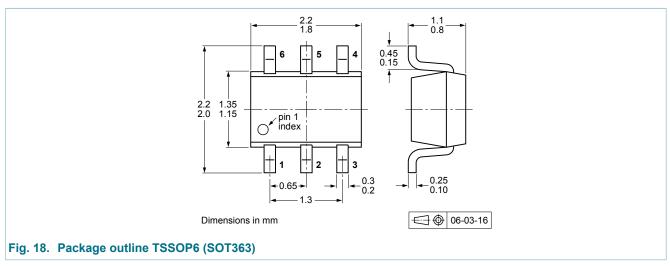
#### 20 V, single N-channel Trench MOSFET



## 8. Test information

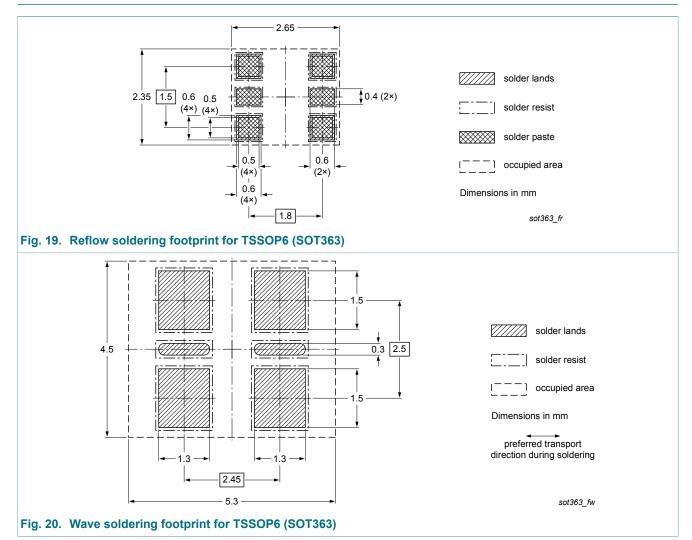


## 9. Package outline



#### 20 V, single N-channel Trench MOSFET

### **10. Soldering**



## 11. Revision history

Table 8.     Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMG45UN v.1	20121113	Product data sheet	-	-	

PMG45UN

#### 20 V, single N-channel Trench MOSFET

#### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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#### 20 V, single N-channel Trench MOSFET

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